10716249_CLS1.txt Most Frequently Occurring Classifications of Patents Returned From A Search of 10/716,249 on August 12, 2005

```
Combined Classifications
 12 257/E21.651
10 257/301
10 257/E27.092
8 257/E27.094
7 257/296
7 257/305
         257/304
         257/E21.648
         438/392
         257/303
257/311
257/E21.008
         257/E27.089
         438/243
         438/244
    4.
         438/249
         257/306
         257/465
         257/466
257/E21.646
257/E27.096
365/149
438/242
         438/386
257/300
         257/307
         257/382
         257/362
257/448
257/461
257/462
257/618
257/E21.143
257/E21.151
         257/E21.396
         257/E21.538
         257/E21.645
         257/E21.043
257/E21.65
257/E21.652
257/E27.086
257/E27.095
         257/E27.095
         257/E27.112
         257/E27.131
         257/E27.133
         257/E27.133
257/E29.262
257/E29.267
365/182
438/152
438/239
438/254
    2222222
         438/259
         438/270
         438/302
         438/387
438/388
438/389
438/73
         438/977
```

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Titles of Most Frequently Occurring Classifications of Patents Returned
       From A Search of 10/716,249 on August 12, 2005
                        (6 OR, 4 XR)
 10 257/301
                      257 : ACTIVÉ SOLID-STATE DEVICES
            Class
                              ...Enhancement mode or with high resistivity channel (e.g., doping of 10 15 cm -3 or less)
.Having insulated electrode (e.g., MOSFET, MOS diode)
..Insulated gate capacitor or insulated gate
            257/264
            257/288
            257/296
                                   transistor combined with capacitor (e.g., dynamic memory
cell)
            257/301
                              ...Capacitor in trench
                      (3 OR, 4 XR)
257 : ACTIVE SOLID-STATE DEVICES
  7 257/296
            Class
            257/264
                              ... Enhancement mode or with high resistivity
                              channel (e.g., doping of 10 15 cm -3 or less)
.Having insulated electrode (e.g., MOSFET, MOS diode)
..Insulated gate capacitor or insulated gate
            257/288
257/296
                                  transistor combined with capacitor (e.g., dynamic memory
cell)
                      (2 OR, 5 XR)
257 : ACTIVE SOLID-STATE DEVICES
  7 257/305
            Class
                              ...Enhancement mode or with high resistivity channel (e.g., doping of 10 15 cm -3 or less)
            257/264
                              .Having insulated electrode (e.g., MOSFET, MOS
            257/288
            257/296
                              .. Insulated gate capacitor or insulated gate
                                    transistor combined with capacitor (e.g., dynamic
memory cell)
            257/301
                              ...Capacitor in trench
            257/305
                              ....With means to insulate adjacent storage
                                  nodes (e.g., channel stops or field oxide)
  5 257/304
                        (2 OR, 3 XR)
            Class
                      257 : ACTIVE SOLID-STATE DEVICES
            257/264
                              ... Enhancement mode or with high resistivity
                              channel (e.g., doping of 10 15 cm -3 or less)
.Having insulated electrode (e.g., MOSFET, MOS diode)
            257/288
257/296
                              ..Insulated gate capacitor or insulated gate transistor combined with capacitor (e.g., dynamic
memory cell)
            257/301
                              ...Capacitor in trench
            257/304
                              ....Storage node isolated by dielectric from
                                  semiconductor substrate
                      (1 OR, 4 XR)
438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
  5 438/392
            Class
                              MAKING PASSIVE DEVICE (E.G., RESISTOR, CAPACITOR, ETC.)
            438/381
            438/386
                              .Trench capacitor
            438/389
                              ..Including doping of trench surfaces
            438/392
                              ...Doping by outdiffusion from a dopant source layer (e.g.,
doped oxide)
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10716249_CLSTITLES1.txt

PLUS Search Results for S/N 10/716,249, Searched August 12, 2005

The Patent Linguistics Utility System (PLUS) is a USPTO automated search system for U.S. Patents from 1971 to the present. PLUS is a query-by-example search system which produces a list of patents that are most closely related linguistically to the application searched. This search was prepared by the staff of the Scientific and Technical Information Center, SIRA.

5371032	5521111	5187550	6107153	5466636
5414285	4988637	5217918	6121651	5498564
5330936	5223730	5234854	4797373	5543348
6232626	5234856	5262662	4833094	5563433
6500692	6249017	5321285	4958206	5627092
6611037	5026659	5702969	5185292	5670805
6730980	5386131	5732014	5225697	5824582
6767759	4954854	5753549	5309008	5885863
6838742	4967248	5897351	5411905	5892707
5198995	5021355	5900659	5448090	5937296